

# FQA11N90 / FQA11N90\_F109

## N-Channel QFET® MOSFET

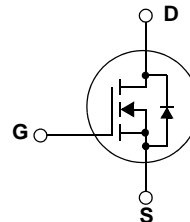
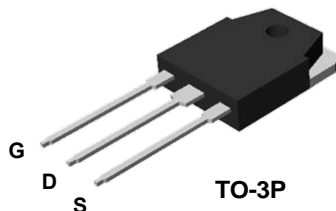
900 V, 11.4 A, 960 mΩ

### Features

- 11.4 A, 900 V,  $R_{DS(on)} = 960 \text{ m}\Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 5.7 \text{ A}$
- Low Gate Charge (Typ. 72 nC)
- Low  $C_{rss}$  (Typ. 30 pF)
- 100% Avalanche Tested
- RoHS Compliant

### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.



### Absolute Maximum Ratings

Symbol	Parameter	FQA11N90	Unit
$V_{DSS}$	Drain-Source Voltage	900	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ )	11.4	A
	- Continuous ( $T_C = 100^\circ\text{C}$ )	7.2	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	45.6	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	1000	mJ
$I_{AR}$	Avalanche Current (Note 1)	11.4	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	30	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ (Note 3)	4.0	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ )	300	W
	- Derate above $25^\circ\text{C}$	2.38	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	FQA11N90	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.42	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	$^\circ\text{C}/\text{W}$

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQA11N90	FQA11N90	TO-3P	--	--	30
FQA11N90	FQA11N90_F109	TO-3PN	--	--	30

## Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

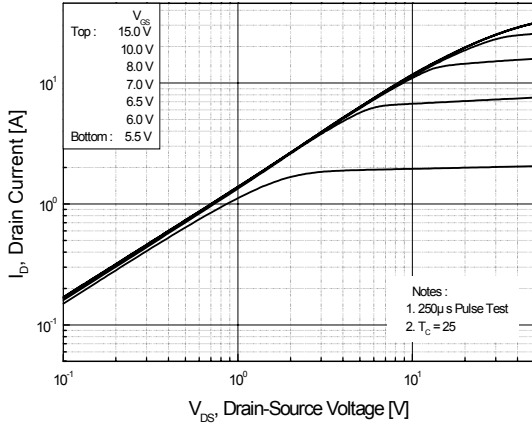
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	900	--	--	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	--	1.0	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 900 V, V <sub>GS</sub> = 0 V	--	--	10	μA
		V <sub>DS</sub> = 720 V, T <sub>C</sub> = 125°C	--	--	100	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V	--	--	-100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	3.0	--	5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5.7 A	--	0.75	0.96	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 5.7 A (Note 4)	--	12	--	S
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz	--	2700	3500	pF
C <sub>oss</sub>	Output Capacitance		--	260	340	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	30	40	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 450 V, I <sub>D</sub> = 11.4A, R <sub>G</sub> = 25 Ω  (Note 4, 5)	--	65	140	ns
t <sub>r</sub>	Turn-On Rise Time		--	135	280	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	165	340	ns
t <sub>f</sub>	Turn-Off Fall Time		--	90	190	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 720 V, I <sub>D</sub> = 11.4A, V <sub>GS</sub> = 10 V  (Note 4, 5)	--	72	94	nC
Q <sub>gs</sub>	Gate-Source Charge		--	16	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	35	--	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	11.4	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	45.6	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 11.4 A	--	--	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 11.4 A, dI <sub>F</sub> / dt = 100 A/μs  (Note 4)	--	850	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	11.2	--	μC

### NOTES:

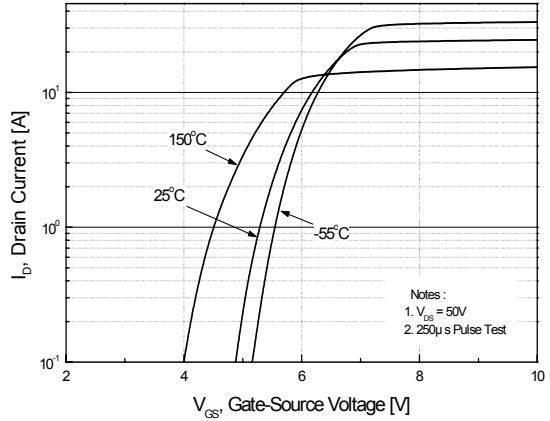
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 15mH, I<sub>AS</sub> = 11.4A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤ 11.4A, di/dt ≤ 200A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

## Typical Performance Characteristics

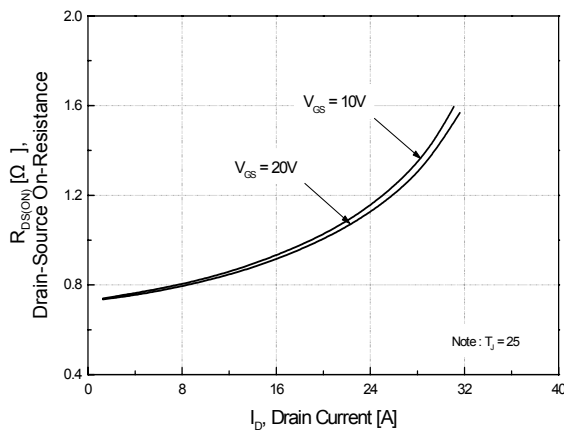
**Figure 1. On-Region Characteristics**



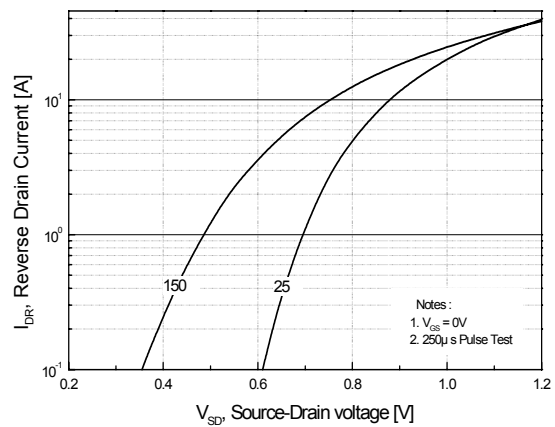
**Figure 2. Transfer Characteristics**



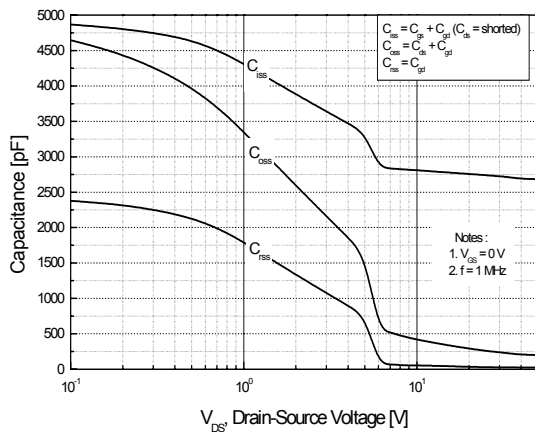
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



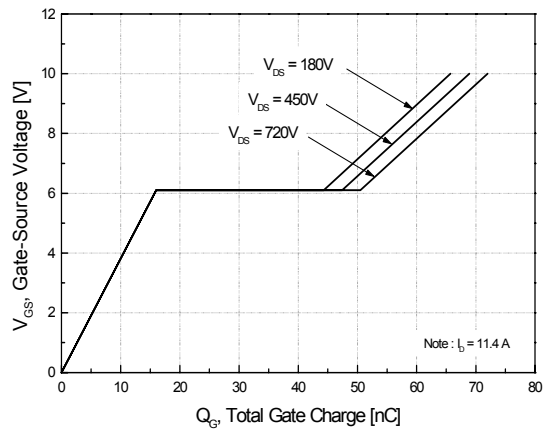
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

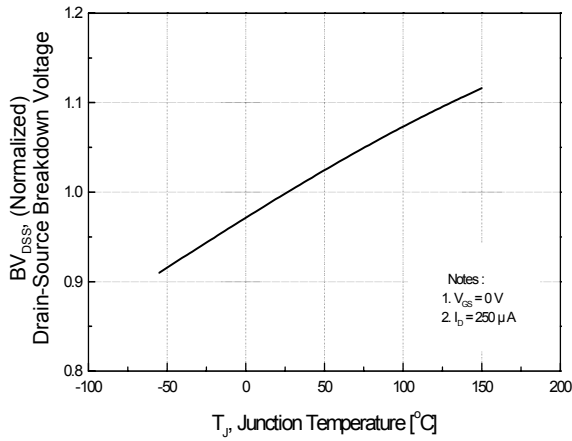


**Figure 6. Gate Charge Characteristics**

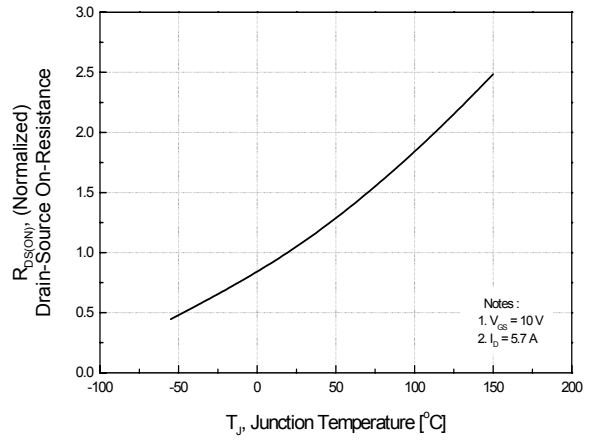


**Typical Performance Characteristics** (Continued)

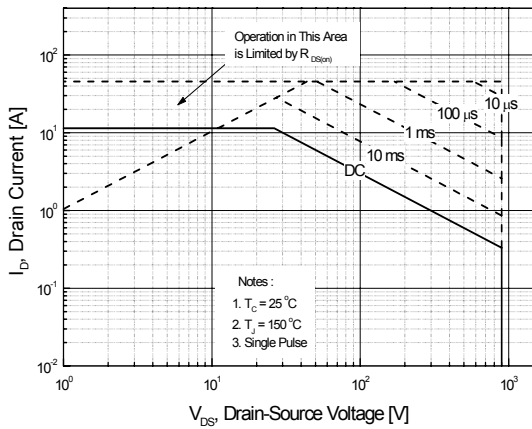
**Figure 7. Breakdown Voltage Variation vs. Temperature**



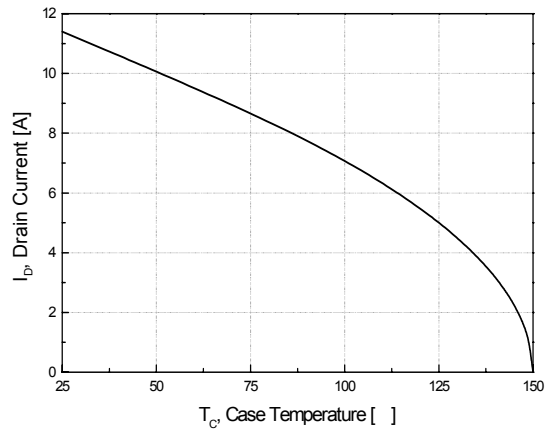
**Figure 8. On-Resistance Variation vs. Temperature**



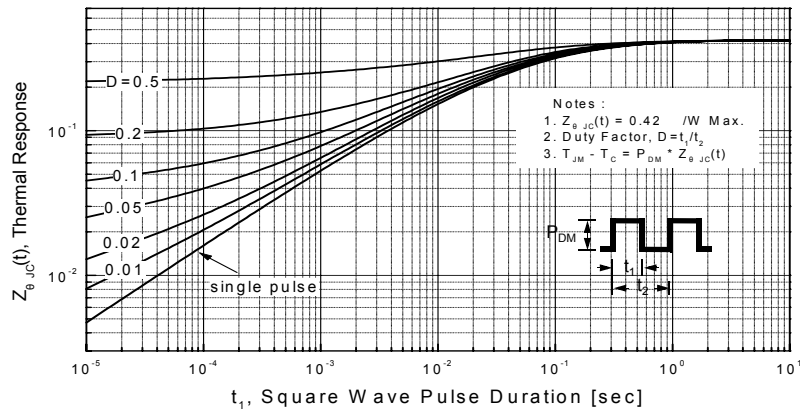
**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**



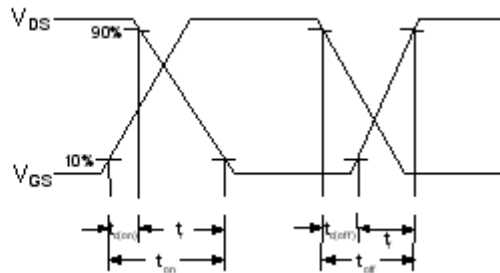
**Figure 11. Transient Thermal Response Curve**



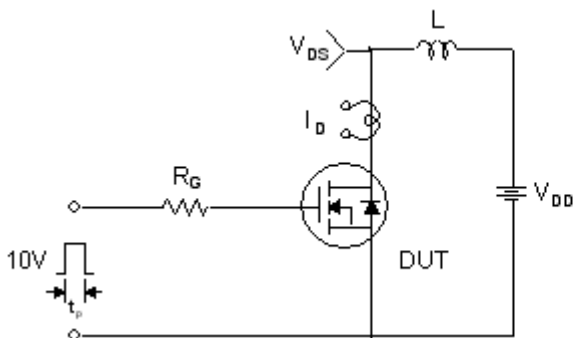
**Gate Charge Test Circuit & Waveform**



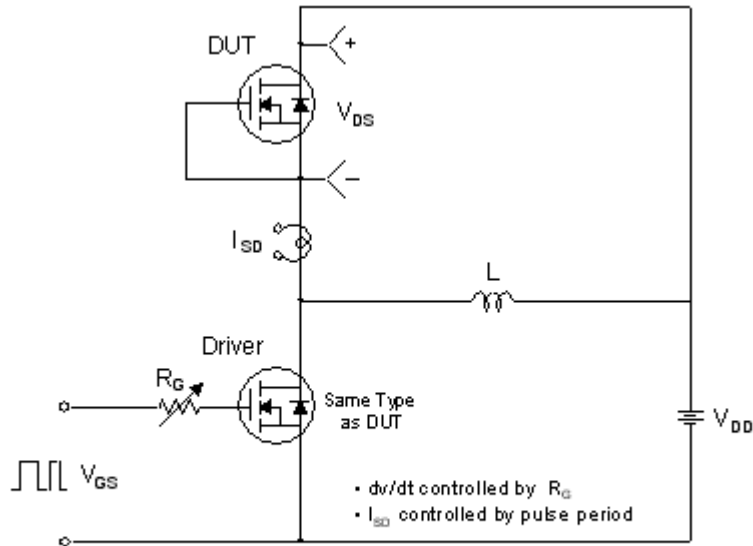
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

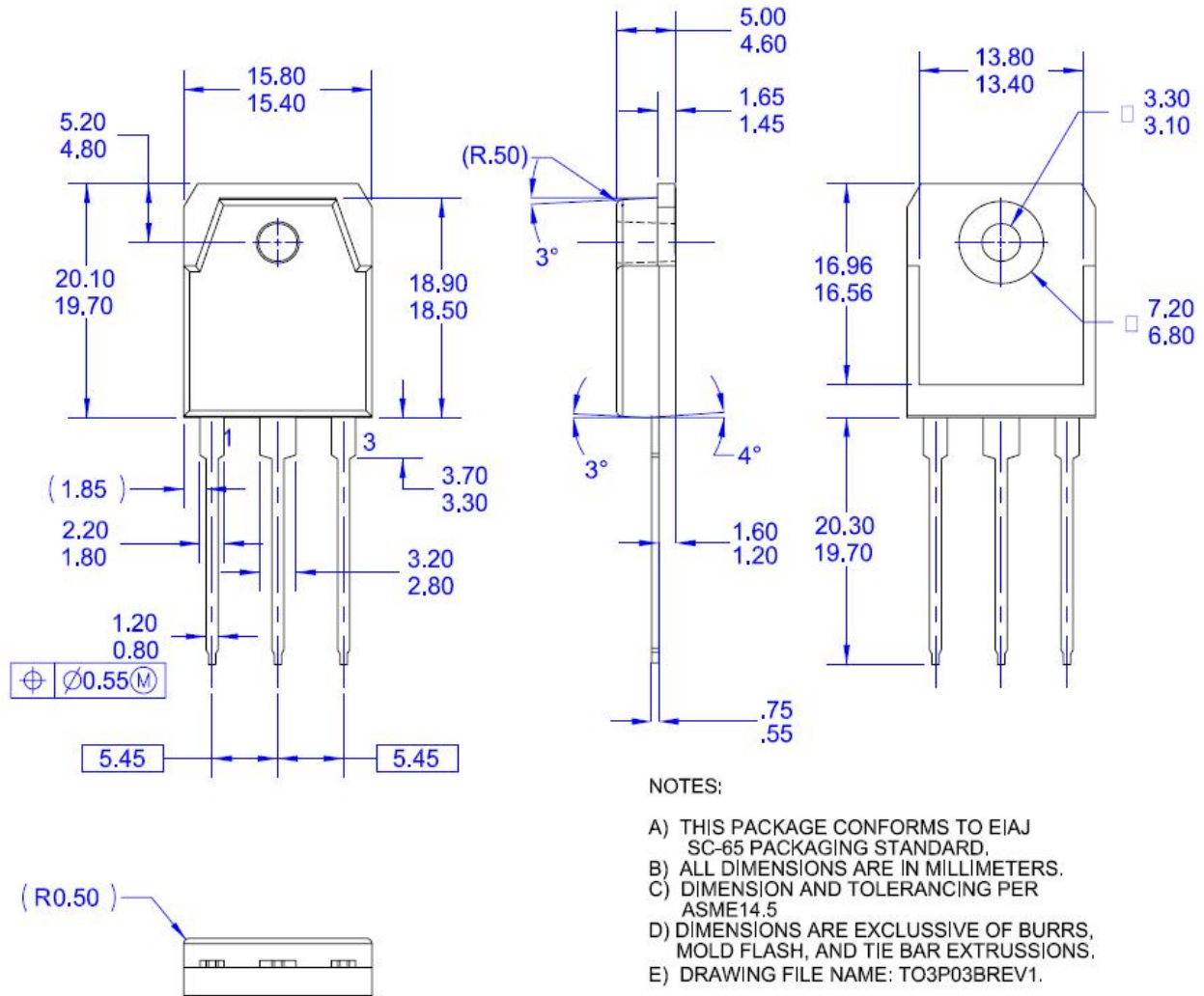


Peak Diode Recovery dv/dt Test Circuit & Waveforms



**Mechanical Dimensions**

**TO-3P**

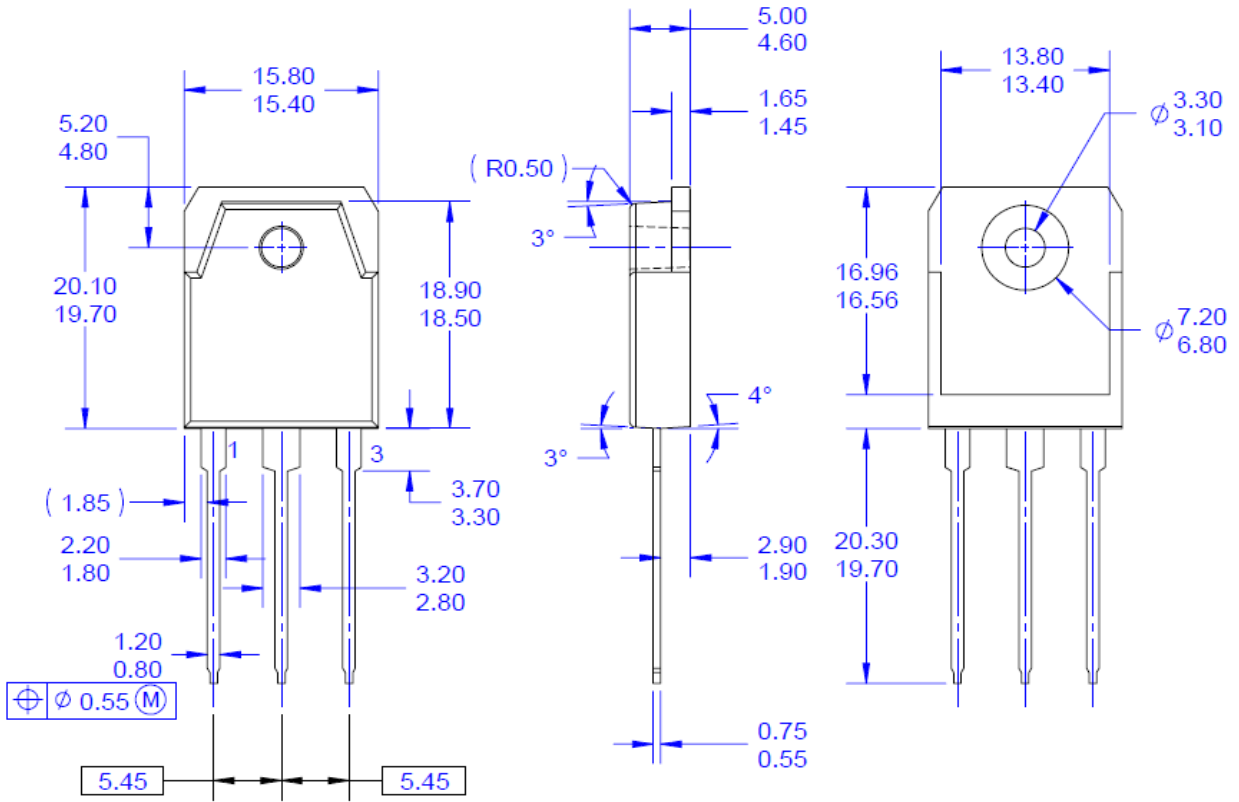


- NOTES:
- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSION AND TOLERANCING PER ASME14.5
  - D) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
  - E) DRAWING FILE NAME: TO3P03BREV1.

Dimensions in Millimeters

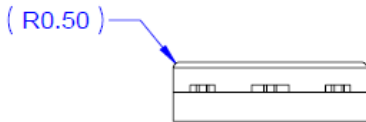
**Mechanical Dimensions**

**TO-3PN**



NOTES: UNLESS OTHERWISE SPECIFIED

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- C) DIMENSION AND TOLERANCING PER ASME14.5
- D) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- E) THIS PACKAGE IS INTENDED ONLY FOR TO3PN.
- F) DRAWING FILE NAME: TO3P03AREV4.



Dimensions in Millimeters



